

FORM 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)	Docket Number: STFD.035US	Application Number: 10/518,779
	Applicant: GOPALAKRISHNAN <i>et al.</i>	
	Filing Date: 12/17/2004	Group Art Unit: Unassigned

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
	5,985,727	11/16/1999	BURR				
	5,677,215	10/14/1997	GOO				
	4,062,699	12/13/1977	ARMSTRONG				
	6,294,818	09/25/2001	FUJIHIRA				
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FOREIGN PATENT DOCUMENTS							
	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
	12/1980	J. Plummer, B. Scharf. "Insulated-Gate Planar Thyristors: I-Structure and Basic Operation." <i>IEEE Transactions on Electron Devices</i> , Vol. ED-27, No. 2. February 1980. pp. 380-386. BEST COPY AVAILABLE					
	01/1976	M. Declercq and J. Plummer. "Avalanche Breakdown in High-Voltage D-MOS Devices." <i>IEEE Transactions on Electron Devices</i> , Vol. ED-23, No. 1. January 1976. pp. 1-4. BEST COPY AVAILABLE					
	9/17/1997	Z.S. Gribnikov et al. "The Tunnel Diode as a Thyristor Emitter." <i>Solid-State Electronics</i> , Vol. 42, No. 9. 17 September 1997. pp 1761- 1763. BEST COPY AVAILABLE					
	11/1998	D. M. Kim. "Electrical Characteristics of Npn-AlGaAs/GaAs HBTs with Modulated Base Doping Structures." <i>Journal of the Korean Physical Society</i> , Vol. 33, No. 5. November 1998, pp. 607-611.					

EXAMINER /Sarah Salerno/	DATE CONSIDERED /S.K.S./
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.	